

# CMS15P03Q8-HF

P-Channel

RoHS Device

Halogen Free



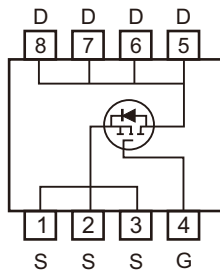
## Features

- Simple drive requirement.
- Low on-resistance.
- Fast switching speed.

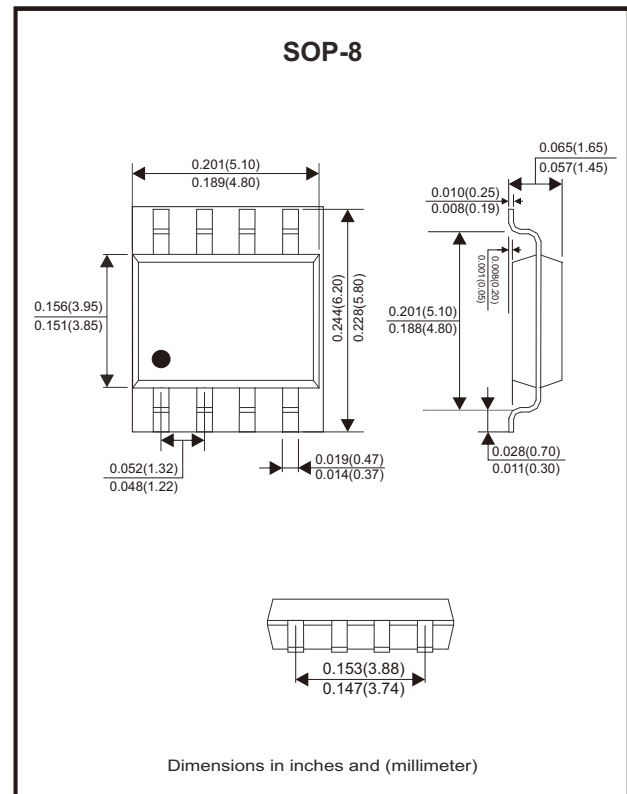
## Mechanical data

- Epoxy : UL 94V-0 rated flame retardant.
- Case : SOP-8, molded plastic.
- Lead : Pure tin plated.

## Circuit Diagram



G : Gate  
S : Source  
D : Drain



## Absolute Maximum Ratings (at Ta=25°C unless otherwise noted)

| Parameter                                                             | Symbol            | Value                        | Unit |
|-----------------------------------------------------------------------|-------------------|------------------------------|------|
| Drain-source breakdown voltage                                        | BV <sub>DSS</sub> | -30                          | V    |
| Gate-source voltage                                                   | V <sub>GS</sub>   | ±25                          | V    |
| Continuous drain current @ T <sub>A</sub> =25°C                       | I <sub>D</sub>    | -15                          | A    |
| Continuous drain current @ T <sub>A</sub> =100°C                      | I <sub>D</sub>    | -9.5                         | A    |
| Pulsed drain current (Note 1)                                         | I <sub>DM</sub>   | -160                         | A    |
| Avalanche current                                                     | I <sub>AS</sub>   | -15                          | A    |
| Avalanche energy @ L=0.1mH, I <sub>D</sub> =-15A, R <sub>G</sub> =25Ω | E <sub>AS</sub>   | 11.25                        | mJ   |
| Power dissipation (Note 2)                                            | P <sub>D</sub>    | T <sub>A</sub> =25°C<br>3.1  | W    |
|                                                                       |                   | T <sub>A</sub> =100°C<br>1.2 |      |
| Operating junction temperature range                                  | T <sub>J</sub>    | -55 to +150                  | °C   |
| Storage temperature range                                             | T <sub>STG</sub>  | -55 to +150                  | °C   |

Notes: 1. Pulse width limited by maximum junction temperature.  
2. Surface mounted on 1 in<sup>2</sup> copper pad of FR-4 board, t ≤ 10s.

Company reserves the right to improve product design, functions and reliability without notice.

REV:C

**Electrical Characteristics** (TA=25°C unless otherwise noted)

| Parameter                                 | Symbol              | Conditions                                                                                    | Min | Typ   | Max  | Unit |
|-------------------------------------------|---------------------|-----------------------------------------------------------------------------------------------|-----|-------|------|------|
| Static                                    |                     |                                                                                               |     |       |      |      |
| Drain-source breakdown voltage            | BV <sub>DSS</sub>   | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA                                                 | -30 |       |      | V    |
| Gate-source threshold voltage             | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA                                   | -1  | -1.5  | -2.5 |      |
| Gate-source leakage                       | I <sub>GSS</sub>    | V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V                                                  |     |       | ±100 | nA   |
| Zero gate voltage drain current           | I <sub>DSS</sub>    | V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V                                                  |     |       | -1   | μA   |
|                                           | I <sub>DSS</sub>    | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C                          |     |       | -10  |      |
| Drain-source on-state resistance (Note 1) | R <sub>DS(on)</sub> | I <sub>D</sub> = -15A, V <sub>GS</sub> = -10V                                                 |     | 7.7   | 9    | mΩ   |
|                                           |                     | I <sub>D</sub> = -10A, V <sub>GS</sub> = -4.5V                                                |     | 11.4  | 18   |      |
|                                           |                     | I <sub>D</sub> = -10A, V <sub>GS</sub> = -3V                                                  |     | 20.3  | 40   |      |
| Forward transconductance (Note 1)         | G <sub>FS</sub>     | V <sub>DS</sub> = -5V , I <sub>D</sub> = -15A                                                 |     | 28    |      | S    |
| Dynamic                                   |                     |                                                                                               |     |       |      |      |
| Input capacitance                         | C <sub>iss</sub>    | V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz                                        |     | 4022  |      | pF   |
| Output capacitance                        | C <sub>oss</sub>    |                                                                                               |     | 498   |      |      |
| Reverse transfer capacitance              | C <sub>rss</sub>    |                                                                                               |     | 442   |      |      |
| Turn-on delay time (Note 1&2)             | t <sub>d(on)</sub>  | V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V<br>I <sub>D</sub> = -15A , R <sub>G</sub> = 3Ω |     | 21    |      | nS   |
| Turn-on rise time (Note 1&2)              | t <sub>r</sub>      |                                                                                               |     | 19    |      |      |
| Turn-off delay time (Note 1&2)            | t <sub>d(off)</sub> |                                                                                               |     | 57    |      |      |
| Turn-off fall time (Note 1&2)             | t <sub>f</sub>      |                                                                                               |     | 22    |      |      |
| Total gate charge (Note 1&2)              | Q <sub>g</sub>      | V <sub>DS</sub> = -15V, I <sub>D</sub> = -15A, V <sub>GS</sub> = 10V                          |     | 56    |      | nC   |
| Total gate charge (Note 1&2)              | Q <sub>g</sub>      | V <sub>DS</sub> = -15V, I <sub>D</sub> = -15A, V <sub>GS</sub> = 4.5V                         |     | 36    |      |      |
| Gate-soutce charge (Note 1&2)             | Q <sub>gs</sub>     | V <sub>DS</sub> = -15V, I <sub>D</sub> = -15A, V <sub>GS</sub> = -10V                         |     | 15    |      |      |
| Gate-drain charge (Note 1&2)              | Q <sub>gd</sub>     |                                                                                               |     | 18    |      |      |
| Gate resistance                           | R <sub>g</sub>      | V <sub>GS</sub> = 15mV, V <sub>DS</sub> = 0, f = 1MHz                                         |     | 3     |      |      |
| Source-Drain Diode                        |                     |                                                                                               |     |       |      |      |
| Continuous source-drain diode current     | I <sub>S</sub>      |                                                                                               |     |       | -10  | A    |
| Pulse diode forward current (Note 3)      | I <sub>SM</sub>     |                                                                                               |     |       | -40  |      |
| Body diode voltage (Note 1)               | V <sub>SD</sub>     | I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0V                                        |     | -0.81 | -1.2 | V    |
| Reverse recovery time                     | t <sub>rr</sub>     | I <sub>F</sub> = -10A, dI <sub>F</sub> /dt = 100A/μs                                          |     | 32    |      | nS   |
| Recovered charge                          | Q <sub>rr</sub>     |                                                                                               |     | 26    |      | nC   |
| Source-Drain Diode                        |                     |                                                                                               |     |       |      |      |
| Thermal resistance                        | R <sub>ΘJC</sub>    | Junction to case                                                                              |     | 22    | 25   | °C/W |
|                                           | R <sub>ΘJA</sub>    | Junction to ambient (Note 4)                                                                  |     | 33    | 40   |      |

Notes: 1. Pulse test: Pulse width ≤300μs, Duty cycle ≤ 2% .

2. Independent of operating temperature.

3. Pulse width limited by maximum junction temperature.

4. Width mounted on a 1 in<sup>2</sup> pad of 2 oz copper, t≤10s; 125°C/W when mounted on minimum copper pad.

## Rating and Characteristic Curves (CMS15P03Q8-HF)

Fig.1 - Typical Output Characteristics

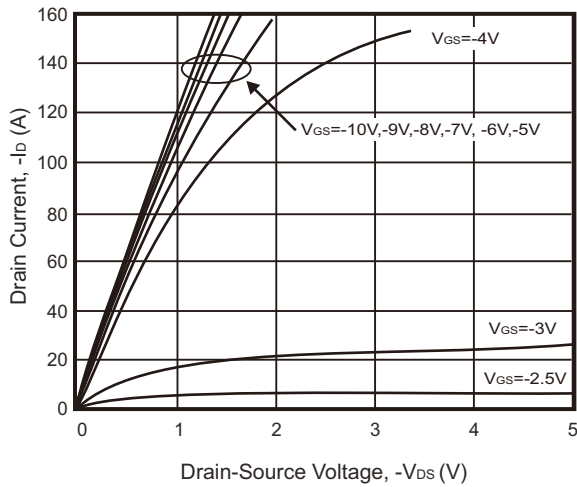


Fig.2 - Static Drain-Source On-State Resistance VS Drain Current

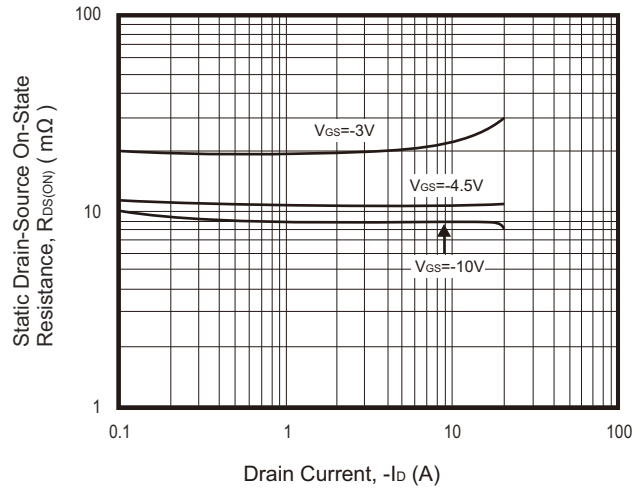


Fig.3 - Static Drain-Source On-State Resistance VS Gate-Source Voltage

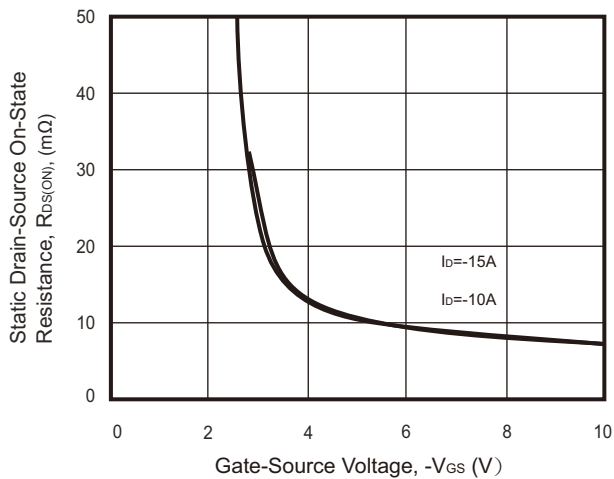


Fig.4 - Capacitance VS Drain-Source Voltage

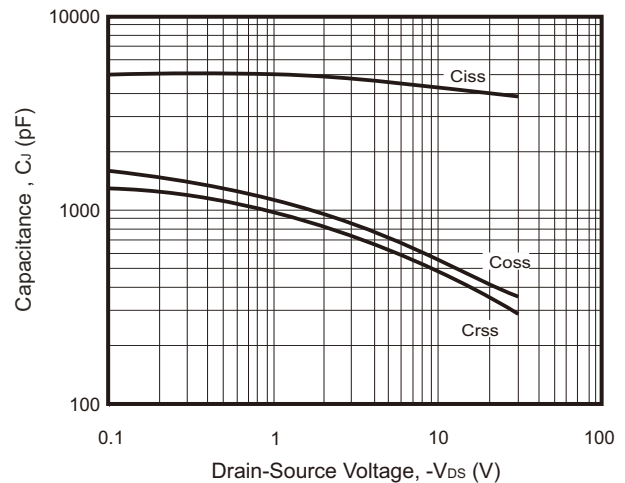


Fig.5 - Forward Transfer Admittance vs Drain Current

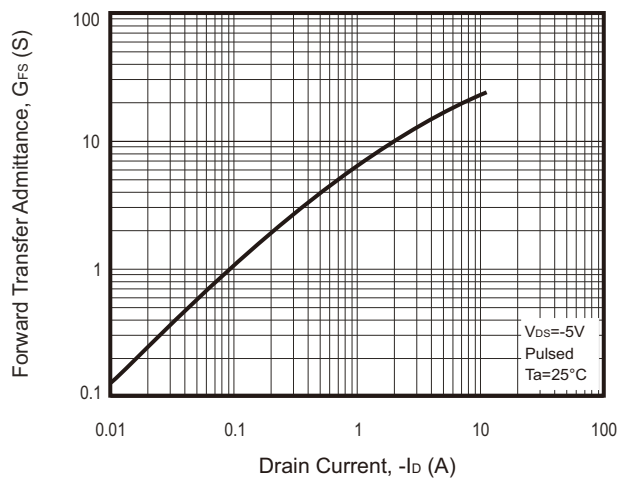
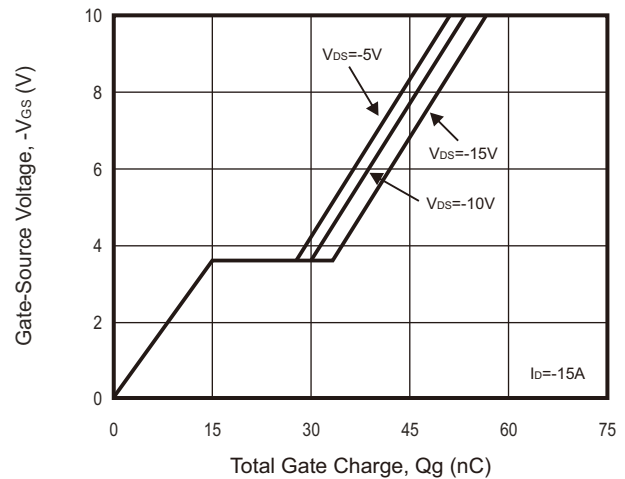
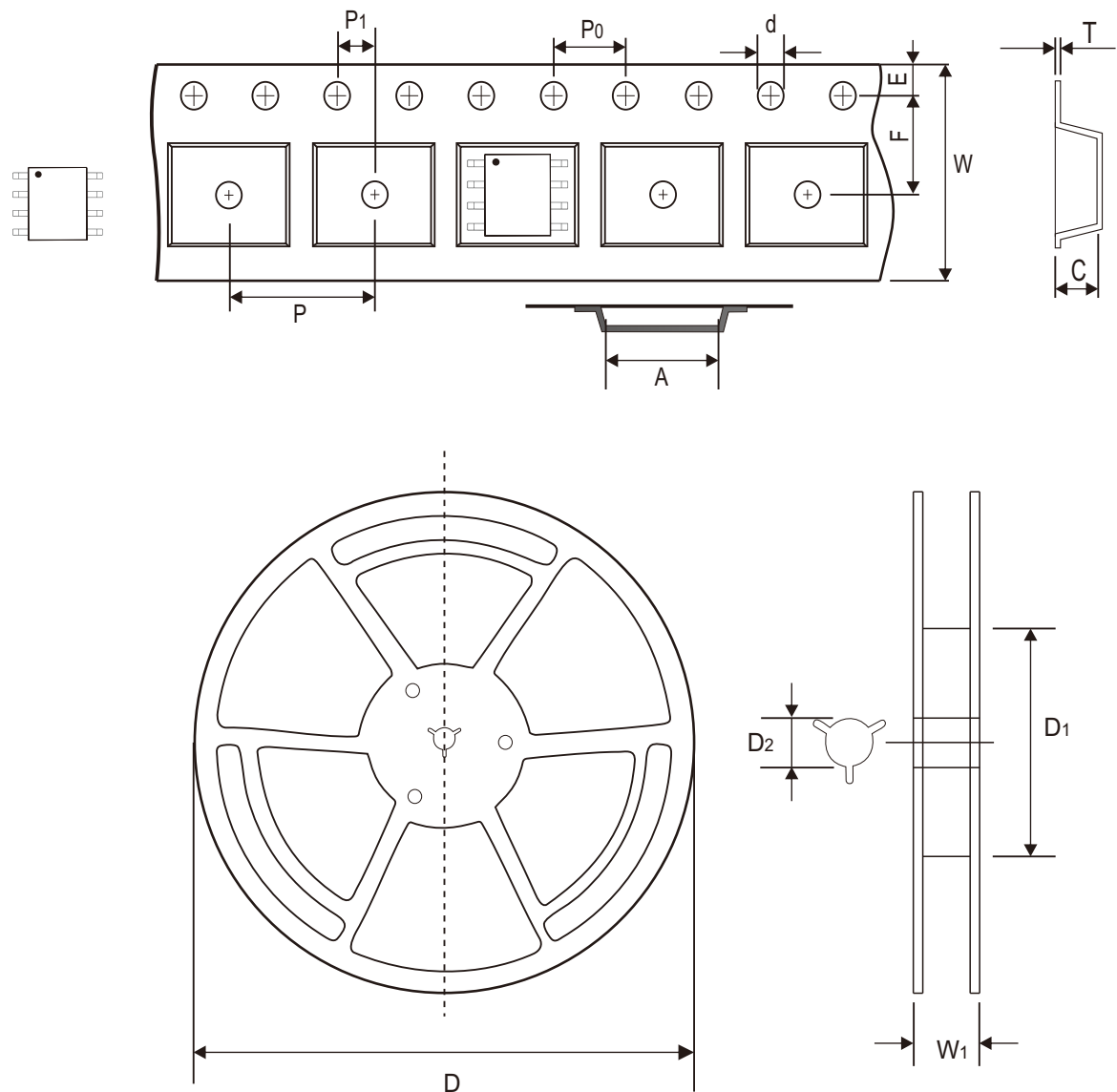


Fig.6 - Gate Charge Characteristics



Reel Taping Specification

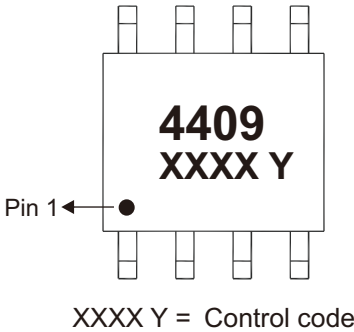


| SOP-8 | SYMBOL | A             | B             | C             | d                        | D              | D1            | D2            |
|-------|--------|---------------|---------------|---------------|--------------------------|----------------|---------------|---------------|
|       | (mm)   | 6.40 ± 0.10   | 5.20 ± 0.10   | 2.10 ± 0.10   | 1.50 + 0.10<br>- 0.00    | 330.00 ± 1.00  | 100.00 ± 0.50 | 13.00 ± 0.20  |
|       | (inch) | 0.252 ± 0.004 | 0.205 ± 0.004 | 0.083 ± 0.004 | 0.059 + 0.004<br>- 0.000 | 12.992 ± 0.039 | 3.937 ± 0.020 | 0.512 ± 0.008 |

| SOP-8 | SYMBOL | E             | F             | P             | P0            | P1            | T             | W                        | W1                       |
|-------|--------|---------------|---------------|---------------|---------------|---------------|---------------|--------------------------|--------------------------|
|       | (mm)   | 1.75 ± 0.10   | 5.50 ± 0.05   | 8.00 ± 0.10   | 4.00 ± 0.10   | 2.00 ± 0.05   | 0.25 ± 0.02   | 12.00 + 0.30<br>- 0.10   | 17.60 + 1.00<br>- 0.00   |
|       | (inch) | 0.069 ± 0.004 | 0.217 ± 0.002 | 0.315 ± 0.004 | 0.157 ± 0.004 | 0.079 ± 0.002 | 0.010 ± 0.001 | 0.472 + 0.012<br>- 0.004 | 0.693 + 0.039<br>- 0.000 |

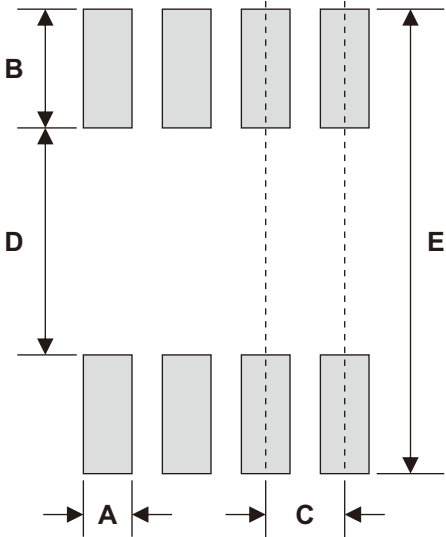
Marking Code

| Part Number   | Marking Code |
|---------------|--------------|
| CMS15P03Q8-HF | 4409         |



Suggested P.C.B. PAD Layout

| SIZE | SOP-8 |        |
|------|-------|--------|
|      | (mm)  | (inch) |
| A    | 0.60  | 0.024  |
| B    | 1.52  | 0.060  |
| C    | 1.27  | 0.050  |
| D    | 4.00  | 0.157  |
| E    | 7.00  | 0.276  |



Standard Packaging

| Case Type | REEL PACK       |                     |
|-----------|-----------------|---------------------|
|           | REEL<br>( pcs ) | Reel Size<br>(inch) |
| SOP-8     | 4,000           | 13                  |